

ABSTRACT OF THE DISCLOSURE

The object of the present invention is to provide a semiconductor memory device wherein analog data signal potential read out from a memory cell to bit-line (bit-line read-out potential) can be measured precisely. In this invention, a sense part circuit block 140 differentially amplifies data signal occurring on one of a pair of bit-lines (for example, bit-line BLN_k, BLT_k) in a memory cell array 110, and reference signal occurring on another of the pair, and data is read out. Bit-lines BLN₁, BLT₁, -, BLN_n, BLT_n are connected to a reference potential setup circuit block 150. Reference potential setup circuit 150 sets up potential assigned from outside of the device as potential of reference signal on bit-line. Bit-line read-out potential is indirectly obtained from the differential amplification result by controlling the reference potential with the reference potential setup circuit block 150.

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